THINKI SEMICONDUCTOR ®

Pb Free Plating Product

BYM26A/BYM26B/BYM26C/BYM26D/BYM26E

2.3 Amperes Glass Passivated Ultra Fast Recovery Rectifier Diode

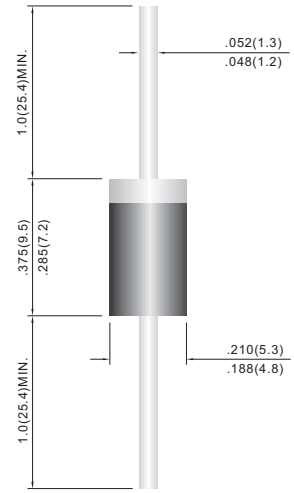
Features

- ✧ Glass passivated chip junction.
- ✧ High efficiency, Low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ Low power loss

Mechanical Data

- ✧ Cases: Molded plastic
- ✧ Epoxy: UL 94V-0 rate flame retardant
- ✧ Lead: Pure tin plated, lead free., solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: Color band denotes cathode
- ✧ High temperature soldering guaranteed: 260 °C /10 seconds/.375",(9.5mm) lead lengths at 5 lbs.,(2.3kg) tension
- ✧ Weight: 1.9 gram approximately

DO-201AD/DO-27 Unit: inch(mm)



Maximun Ratings and Electrical Characteristics at 25 °C

Marking Code		BYM26A	BYM26B	BYM26C	BYM26D	BYM26E
V_{RRM}	Peak Recurrent Reverse Voltage (V)	200	400	600	800	1000
V_{RMS}	Maximum RMS Voltage (V)	140	280	420	560	700
V_{DC}	Maximum DC Blocking Voltage (V)	200	400	600	800	1000
$I_{F(AV)}$	Forward Current at Tamb = 55 °C	2.3 A				
I_{FRM}	Recurrent Peak Forward Current	19 A				
I_{FSM}	10 ms.Peak Sine Wave Forward Surge Current	45 A				
t_{rr}	Max. Reverse Recovery Time From I_F = 0.5 A; I_R = 1 A; I_{rr} = 0.25 A	30 ns			75 ns	
V_{BR}	Avalanche breakdown voltage at 100 µA (V)	>300	>500	>700	>900	>1100
T_j	Operating Temperature Range	-65 to +175 °C				
T_{stg}	Storage Temperature Range	-65 to +175 °C				
E_{RSM}	Maximum non Repetitive Peak Reverse Avalanche Energy. I_R = 1 A; T_j = 25 °C	20 mJ				

Electrical Characteristics at Tamb = 25 °C

V_F	Max. Forward Voltage Drop at I_F = 2 A	at 25 °C at 175 °C	2.65 V 1.34 V
I_R	Max. Reverse Current at V_{RRM}	at 25°C at 165 °C	5 µA 150 µA
$R_{th\ (j-a)}$	Max. Thermal Resistance (l = 10 mm)		30 °C/W

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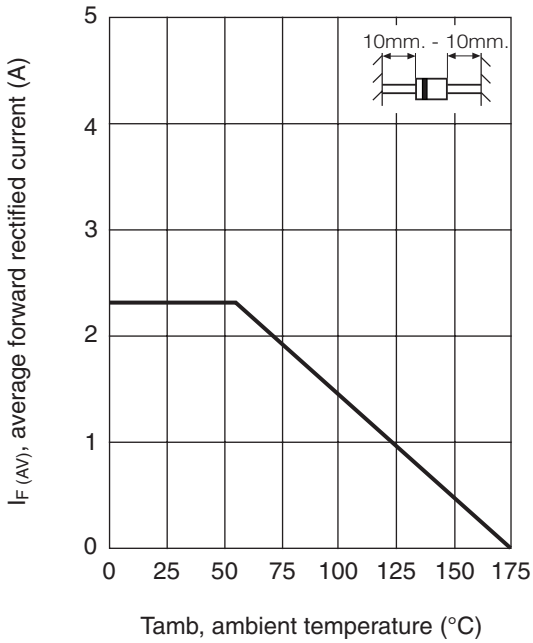
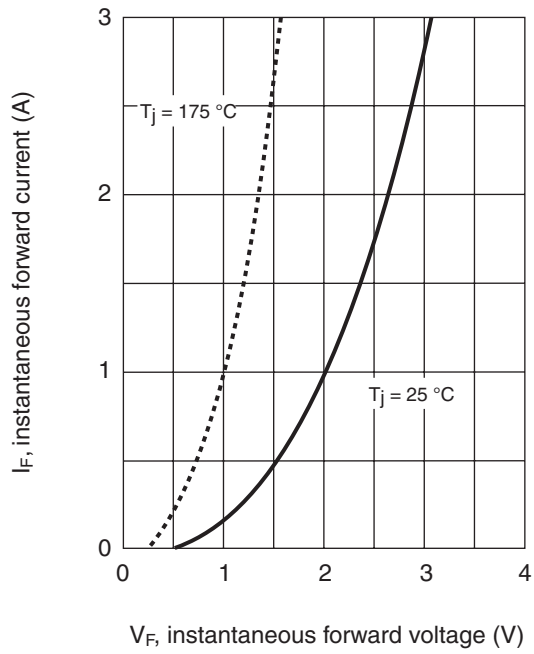
Ratings and Characteristics (Ta 25 °C unless otherwise noted)

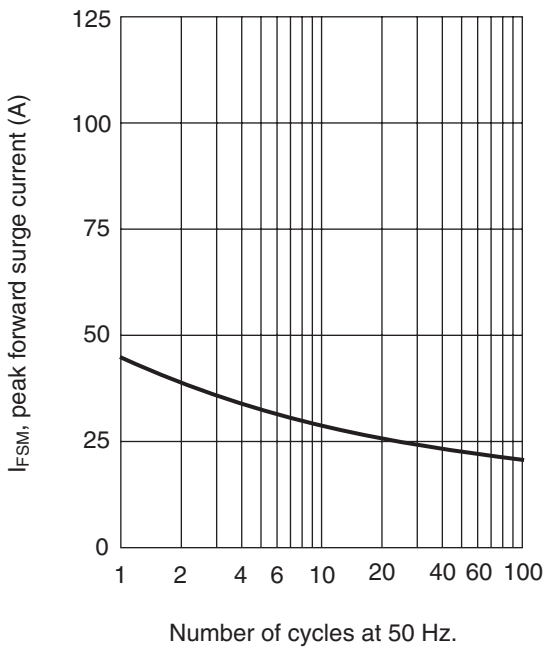
FORWARD CURRENT DERATING CURVE



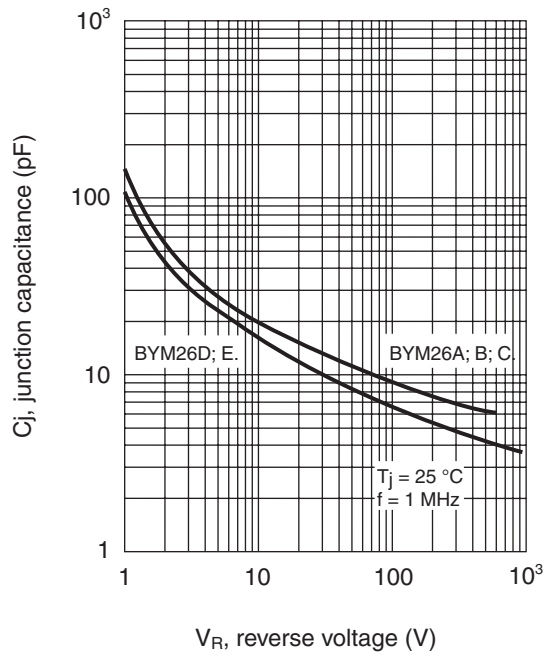
MAXIMUM FORWARD CHARACTERISTIC



MAXIMUM NON REPETITIVE PEAK FORWARD SURGE CURRENT



TYPICAL JUNCTION CAPACITANCE



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